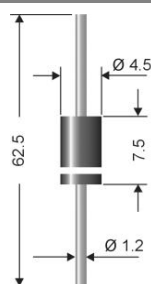


BY 1600...BY 2000



Axial lead diode

Standard silicon rectifier diodes

BY 1600...BY 2000

Forward Current: 3 A

Reverse Voltage: 1600 to 2000 V

Features

- Max. solder temperature: 260°C
- Plastic material has UL classification 94V-0

Mechanical Data

- Plastic case DO-201
- Weight approx.: 1 g
- Terminals: plated terminals solderable per MIL-STD-750
- Mounting position: any
- Standard packaging: 1700 pieces per ammo

¹⁾ Valid, if leads are kept at ambient temperature at a distance of 10 mm from case

²⁾ $I_F = 3A$, $T_J = 25^\circ C$

³⁾ $T_A = 25^\circ C$

Type	Repetitive peak reverse voltage	Surge peak reverse voltage	Max. reverse recovery time	Max. forward voltage
	V_{RRM} V	V_{RSM} V	$I_F = -A$ $I_R = -A$ $I_{RR} = -A$ t_{rr} ns	$V_F^{2)}$
BY 1600	1600	1600	-	1,1
BY 1800	1800	1800	-	1,1
BY 2000	2000	2000	-	1,1

Absolute Maximum Ratings $T_C = 25^\circ C$, unless otherwise specified			
Symbol	Conditions	Values	Units
I_{FAV}	Max. averaged fwd. current, R-load, $T_A = 50^\circ C$ ¹⁾	3	A
I_{FRM}	Repetitive peak forward current $f > 15 Hz$ ¹⁾	20	A
I_{FSM}	Peak forward surge current 50 Hz half sinus-wave ³⁾	80	A
i^2t	Rating for fusing, $t < 10 ms$ ³⁾	32	A ² s
R_{thA}	Max. thermal resistance junction to ambient ¹⁾	25	K/W
R_{thT}	Max. thermal resistance junction to terminals ¹⁾	-	K/W
T_J	Operating junction temperature	-50...+150°C	°C
T_s	Storage temperature	-50...+175°C	°C

Characteristics $T_C = 25^\circ C$, unless otherwise specified			
Symbol	Conditions	Values	Units
I_R	Maximum leakage current, $T_J = 25^\circ C$; $V_R = V_{RRM}$	<20	µA
	$T_J = ^\circ C$; $V_R = V_{RRM}$		
C_J	Typical junction capacitance (at MHz and applied reverse voltage of V)	-	pF
Q_{rr}	Reverse recovery charge ($U_R = V$; $I_F = A$; $dI_F/dt = A/ms$)	-	µC
E_{RSM}	Non repetitive peak reverse avalanche energy ($I_R = mA$; $T_J = ^\circ C$; inductive load switched off)	-	mJ

